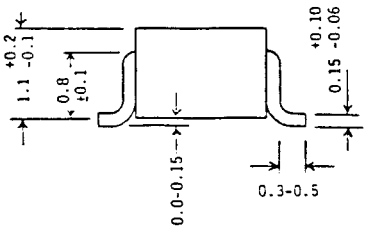
ROHM

CUSTOMER	NO. MMST8098
SUBJECT SOT-23 TRANSISTOR, NPN , SILICON	PAGE 1 of 2
	DATE January 14, 1987

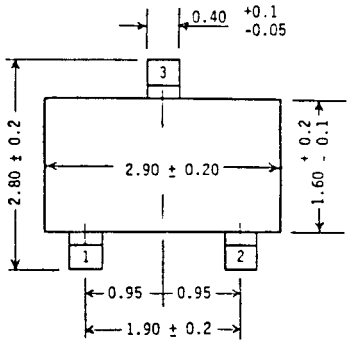
ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)

Collector-Base Voltage	V_{CBO}	60 V
Collector-Emitter Voltage	V_{CEO}	60 V
Emitter-Base Voltage	V_{EBO}	6 V
Collector Current	I_C	200 mA
Power Dissipation-Free Air	P_D	200 mW
Power Dissipation-Ceramic Substrate	P_D	350 mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to 150 °C
Solder Temperature (10 seconds)		260 °C

DIMENSIONS: Units (mm)



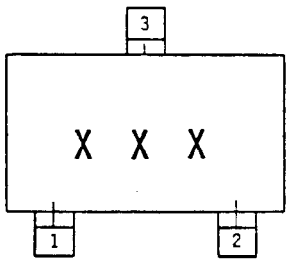
END VIEW



Pin-Out	
1	B
2	E
3	C

THE JAPANESE STYLE SC-59 PACKAGE

MARKING:



Three Digit Marking Code

R A V

PACKAGING:

____ BULK, 500 per BAG
____ MAGAZINES OF 50 EACH
____ 8mm T&R, T-146 3K/REEL
____ 8mm T&R, T-147 3K/REEL
____ 8mm T&R, T-246 10K/REEL
____ 8mm T&R, T-247 10K/REEL

REMARKS: PROCESS: C-22 Thermal Resistance $R_{\theta JA}$ 625 °C/Watt
FREE AIR, T_A = 25°C

ROHM ELECTRONICS
3034 Owen Drive, Antioch, TN 37013
TEL:(615)641-2020 FAX:(615)641-2022

APPROVAL	CHECK	DESIGN
AR 10/12/84		

MASTER

IF SC-4

ROHM

CUSTOMER	NO. MMST8098
	PAGE 2 of 2
SUBJECT TRANSISTOR, NPN ,SILICON SOT-23	DATE January 14, 1987

ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV_{CBO}	I_C = 100 µA	60			V
BV_{CEO}	I_C = 10 mA	60			V
BV_{EBO}	I_E = 10 µA	6			V
I_{CBO}	V_{CB} = 60 V		2.0	100	nA
I_{CEO}	V_{CE} = 60 V		1.5	100	nA
I_{EBO}	V_{EB} = 6 V		1.0	100	nA
h_{FE}	I_C = 1.0 mA, V_{CE} = 5.0 V	100		300	
h_{FE}	I_C = 10 mA, V_{CE} = 5.0 V	100			
h_{FE}	I_C = 100 mA, V_{CE} = 5.0 V	75			
$V_{CE(SAT)}$	I_C = 100 mA, I_B = 5.0 mA			0.4	V
$V_{CE(SAT)}$	I_C = 100 mA, I_B = 10 mA			0.3	V
$V_{BE(ON)}$	I_C = 1.0 mA, V_{CE} = 5.0 V	0.5		0.7	V
f_T	I_C = 10 mA, V_{CE} = 5.0 V, f= 100MHz	150	350		MHz
C_{ob}	V_{CB} = 5.0 V, I_E = 0, f = 1.0 MHz			6.0	pF
C_{ib}	V_{BE} = 5.0 V, I_C = 0, f = 1.0 MHz			25	pF

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